

1765  
Image

Attorney Docket No. 5000.236  
Confirmation No.: 6381

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Jason R. Jenny et al.

Group Art Unit 1765

Serial No.: 10/064,232

Examiner: Matthew A. Anderson

Filed: June 24, 2002

For: METHOD FOR PRODUCING SEMI-INSULATING  
RESISTIVITY IN HIGH PURITY SILICON  
CARBIDE CRYSTALS

November 4, 2003

Commissioner for Patents  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**  
**CITATION UNDER 37 C.F.R. 1.97**

Sir:

Attached is a list of documents on Form PTO/SB/08A, together with a copy of each identified document. Each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign Patent Office in a counterpart foreign application, namely the International Search Report for International Application Number PCT/US03/18068, not more than three months prior to the filing of this Information Disclosure Statement.

We also enclose a copy of this International Search Report. It is requested that the Examiner consider these documents and officially make them of record in accordance with the provisions of 37 C.F.R. § 1.97 and MPEP § 609.

Respectfully submitted,

Philip Summa  
Reg. No. 31,573

021176  
Summa & Allan, P.A.  
11610 North Community House Road, Suite 200  
Ballantyne Corporate Place  
Charlotte, North Carolina 28277-2162  
Telephone: 704-945-6700  
Facsimile: 704-945-6735

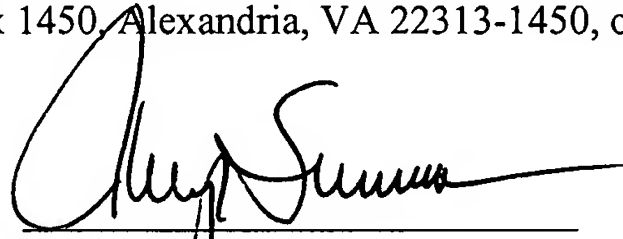
\\Server\F\FIRM DOCS\5000\236\Supp IDS 110403.doc

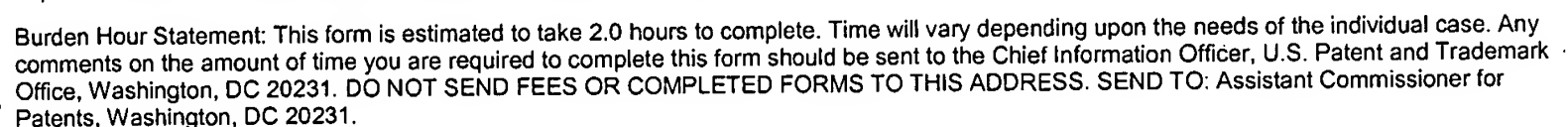


In re: Jason R. Jenny et al.  
Serial No. 10/064,232  
Filed June 24, 2002  
Page 2

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on November 4, 2003.

  
Philip Summa





Please type a plus sign (+) inside this box →



PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031  
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number

Substitute for form 1449A/PTO

## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 2

### Complete if Known

Application Number	10/064,232
Filing Date	June 24, 2002
First Named Inventor	Jason R. Jenny et al.
Group Art Unit	1765
Examiner Name	Matthew A. Anderson
Attorney Docket Number	5000.236

### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	4	S.K. LILOV; <i>Determination of native defect concentrations and deviation from stoichiometry in silicon carbide</i> ; Materials Science & Engineering; April 15, 1993; pages 226-229; Vol. B18, No. 3; Switzerland	
	5	YOH-ICHI YAMAGUCHI ET AL.; <i>Properties of heteroepitaxial 3C-SiC films grown by LPCVD</i> ; Sensors and Actuators A; June 1, 1996; pages 695-699, Vol. 54, No. 1-3; Elsevier Sequoia S.A.; Lausanne, CH	
	6	A. ELLISON ET AL.; <i>HTCVD growth of semi-insulating 4H-SiC crystals with low defect density</i> ; Silicon Carbide-Materials, Processing and Devices Symposium (Materials Research Society Symposium Proceedings Vol. 640) Silicon Carbide-Materials, Processing and Devices Symposium, Boston, MA, USA, 27-29, Nov. 2000, 2001 Warrendale, PA, USA, Mater. Res. Soc., USA, pages H1.2.1 - 11	
	7	VIKTOR V. ZELENIN ET AL.; <i>Growth and investigation of epitaxial 6H-SiC layers obtained by CVD on Lely-grown substrates</i> ; Materials Science and Engineering B; April 1, 1997; pages 300-303; Vol. 46, No. 1-3; Elsevier Sequoia, Lausanne, CH	
	8	SVITLANA I. VLASKINA ET AL.; <i>6H to 3C Polytype Transformation in Silicon Carbide</i> ; Japanese Journal of Applied Physics, Part 2 (Letters); January 15, 1999; pages L27-L29; Vol. 38, No. 1A-B; Publication Office, Japanese Journal Appl. Phys.; Japan	

Examiner  
Signature

Date  
Considered

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.